

N-channel 950 V, 2  $\Omega$  typ., 3.5 A MDmesh™ K5  
Power MOSFETs in DPAK, TO-220FP, TO-220 and IPAK

Datasheet - production data

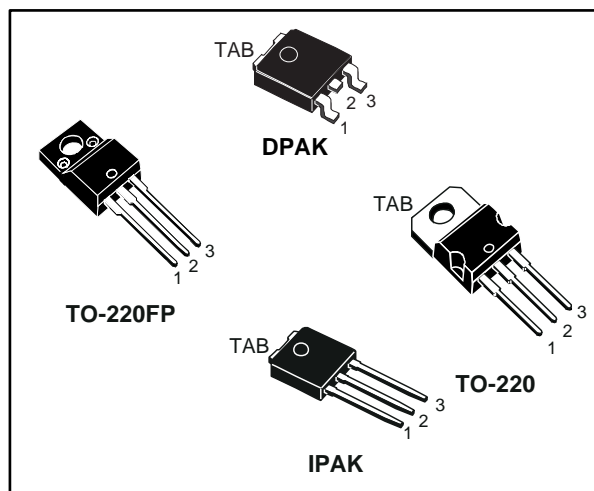
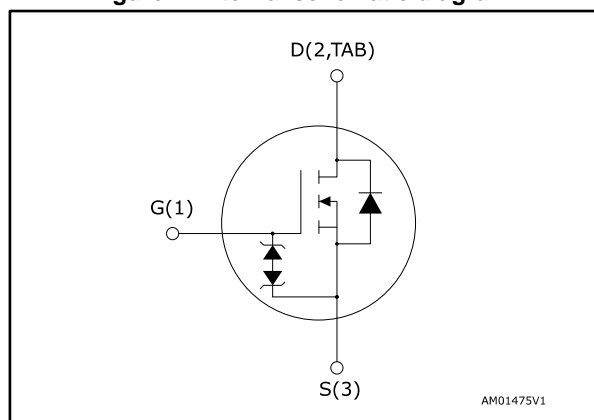


Figure 1: Internal schematic diagram



## Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>	P <sub>tot</sub>
STD5N95K5	950 V	2.5 $\Omega$	3.5 A	70 W
STF5N95K5				25 W
STP5N95K5				70 W
STU5N95K5				70 W

- Industry's lowest R<sub>DS(on)</sub> x area
- Industry's best FoM (figure of merit)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

## Applications

- Switching applications

## Description

These very high voltage N-channel Power MOSFETs are designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1: Device summary

Order code	Marking	Package	Packing
STD5N95K5	5N95K5	DPAK	Tape and reel
STF5N95K5		TO-220FP	Tube
STP5N95K5		TO-220	
STU5N95K5		IPAK	

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# 1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value		Unit
		DPAK, TO-220, IPAK	TO-220FP	
V <sub>GS</sub>	Gate-source voltage	±30		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	3.5	3.5 <sup>(1)</sup>	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	2.2	2.2 <sup>(1)</sup>	A
I <sub>DM</sub> <sup>(2)</sup>	Drain current pulsed	14		A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	70	25	W
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	4.5		V/ns
dv/dt <sup>(4)</sup>	MOSFET dv/dt ruggedness	50		V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T <sub>C</sub> =25 °C)		2500	V
T <sub>j</sub>	Operating junction temperature range	-55 to 150		°C
T <sub>stg</sub>	Storage temperature range			

**Notes:**

- <sup>(1)</sup>Limited by maximum junction temperature.
- <sup>(2)</sup>Pulse width limited by safe operating area.
- <sup>(3)</sup>I<sub>SD</sub> ≤ 3.5 A, di/dt ≤ 100 A/μs, V<sub>DS</sub> (peak) ≤ V<sub>(BR)DSS</sub>
- <sup>(4)</sup>V<sub>DS</sub> ≤ 640 V

Table 3: Thermal data

Symbol	Parameter	Value				Unit
		DPAK	TO-220FP	TO-220	IPAK	
R <sub>thj-case</sub>	Thermal resistance junction-case	1.47	5	1.47		°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient		62.5		100	°C/W
R <sub>thj-pcb</sub> <sup>(1)</sup>	Thermal resistance junction-pcb	50				°C/W

**Notes:**

- <sup>(1)</sup>When mounted on 1 inch<sup>2</sup> FR-4, 2 Oz copper board

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I <sub>AR</sub>	Avalanche current, repetitive or not repetitive (pulse width limited by T <sub>jmax</sub> )	1	A
E <sub>AS</sub>	Single pulse avalanche energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	70	mJ

## 2 Electrical characteristics

$T_C = 25\text{ °C}$  unless otherwise specified

**Table 5: On/off-state**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	950			V
$I_{DSS}$	Zero gate voltage drain current	$V_{DS} = 950\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 950\text{ V}$ , $V_{GS} = 0\text{ V}$ $T_C = 125\text{ °C}^{(1)}$			50	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 1.5\text{ A}$		2	2.5	$\Omega$

**Notes:**

<sup>(1)</sup>Defined by design, not subject to production test.

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	220	-	pF
$C_{oss}$	Output capacitance		-	17	-	pF
$C_{rss}$	Reverse transfer capacitance		-	1	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{ to }760\text{ V}$	-	30	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	11	-	pF
$R_g$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	17	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 760\text{ V}$ , $I_D = 3.5\text{ A}$ $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 19: "Test circuit for gate charge behavior"</a> )	-	12.5	-	nC
$Q_{gs}$	Gate-source charge		-	2	-	nC
$Q_{gd}$	Gate-drain charge		-	10	-	nC

**Notes:**

<sup>(1)</sup> $C_{o(tr)}$  is a constant capacitance value that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

<sup>(2)</sup> $C_{o(er)}$  is a constant capacitance value that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 475\text{ V}$ , $I_D = 1.75\text{ A}$ , $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see <i>Figure 18: "Test circuit for resistive load switching times"</i> and <i>Figure 23: "Switching time waveform"</i> )	-	12	-	ns
$t_r$	Rise time		-	16	-	ns
$t_{d(off)}$	Turn-off delay time		-	32	-	ns
$t_f$	Fall time		-	25	-	ns

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		3.5	A
$I_{SDM}$	Source-drain current (pulsed)		-		14	A
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 3.5\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 3.5\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see <i>Figure 20: "Test circuit for inductive load switching and diode recovery times"</i> )	-	330		ns
$Q_{rr}$	Reverse recovery charge		-	2.2		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	13		A
$t_{rr}$	Reverse recovery time		$I_{SD} = 3.5\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <i>Figure 20: "Test circuit for inductive load switching and diode recovery times"</i> )	-	525	
$Q_{rr}$	Reverse recovery charge	-		3.2		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	-		12		A

**Notes:**

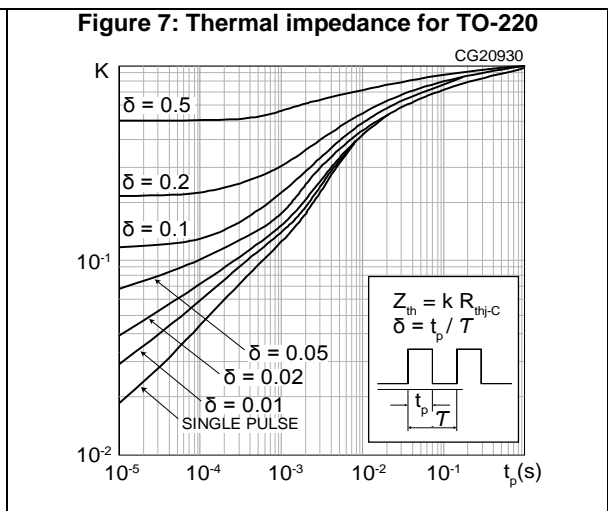
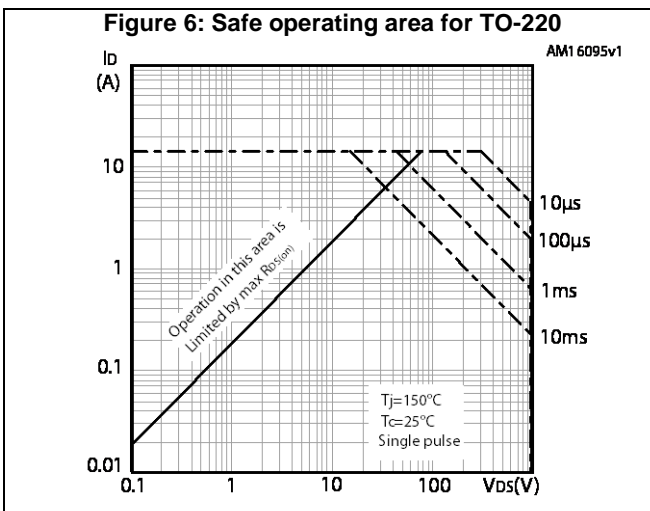
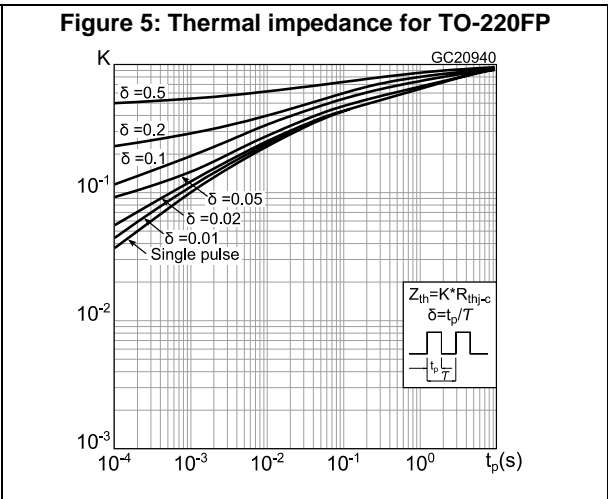
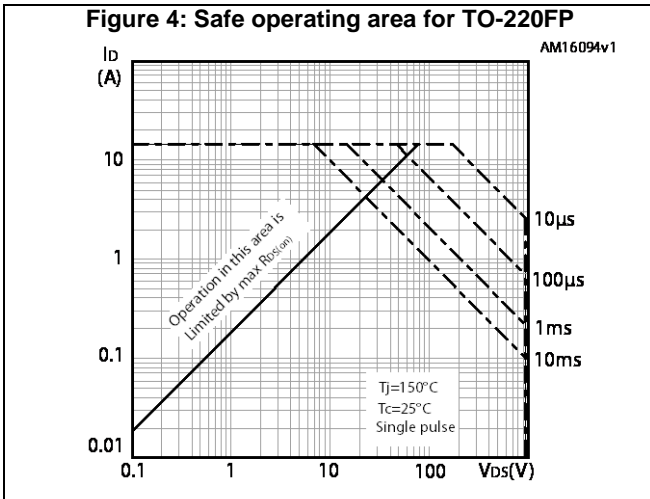
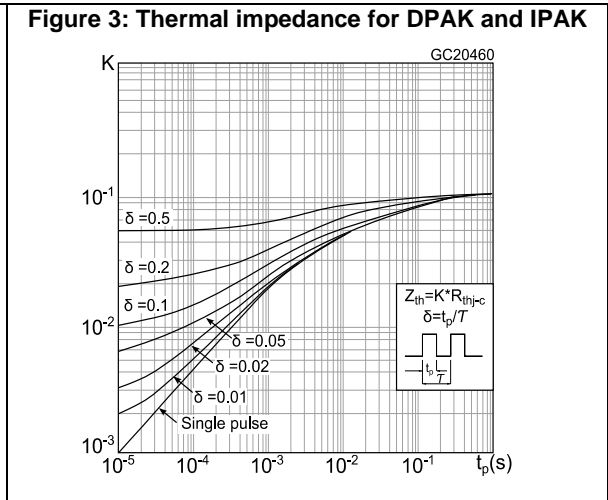
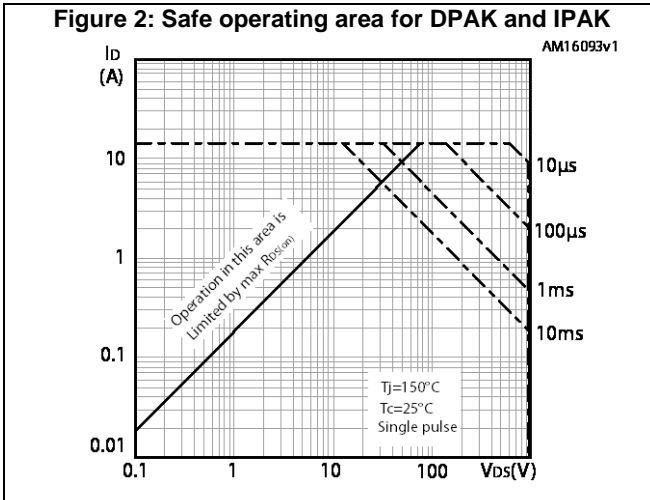
<sup>(1)</sup>Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

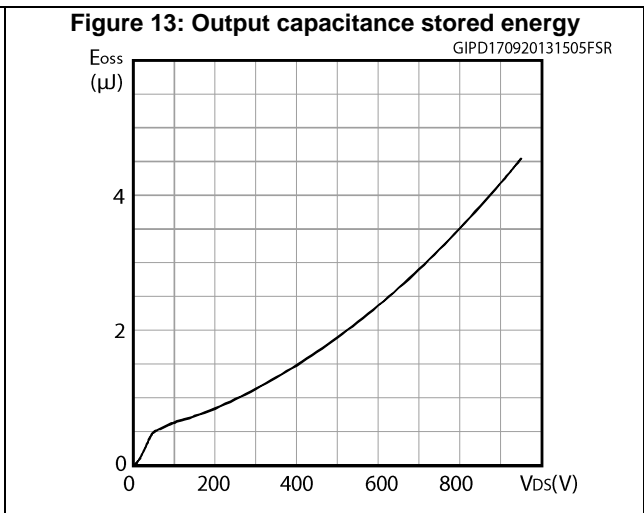
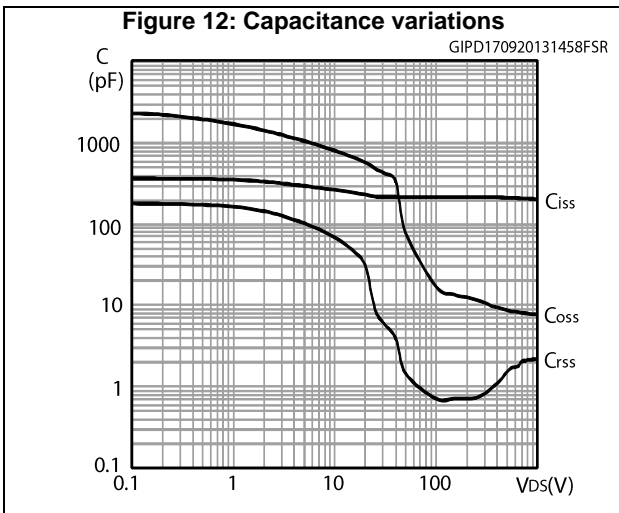
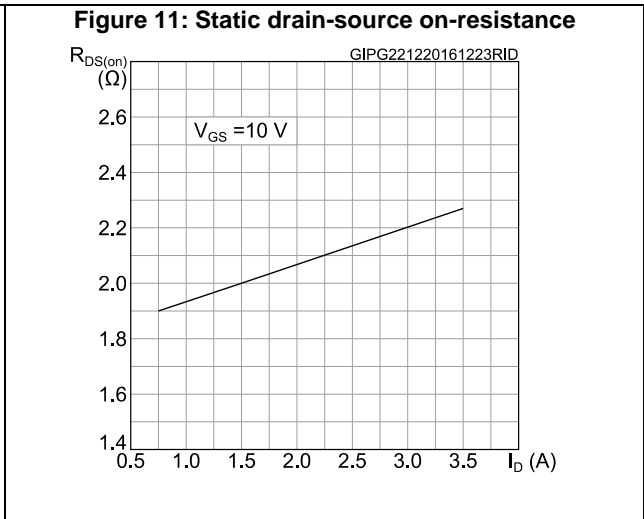
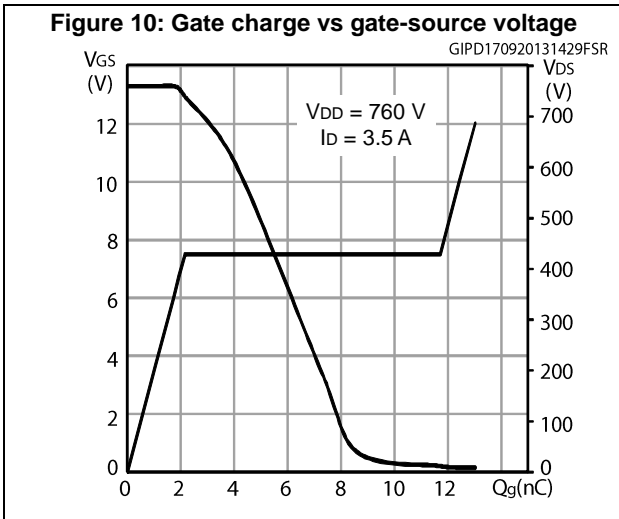
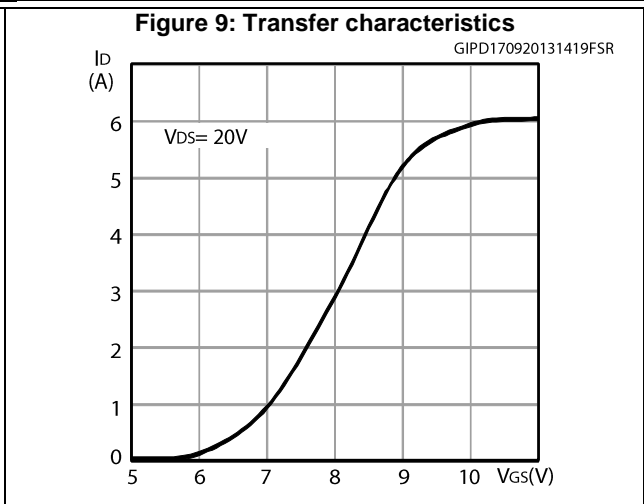
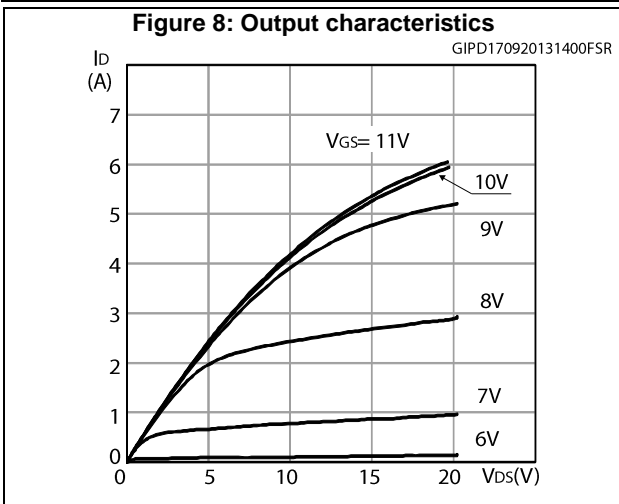
Table 9: Gate-source Zener diode

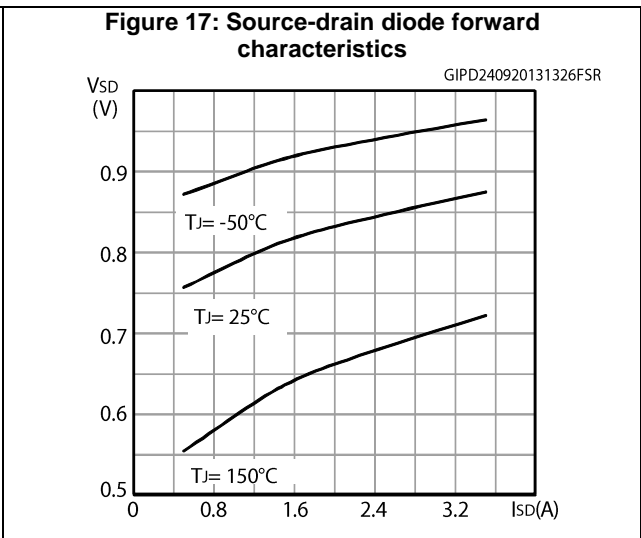
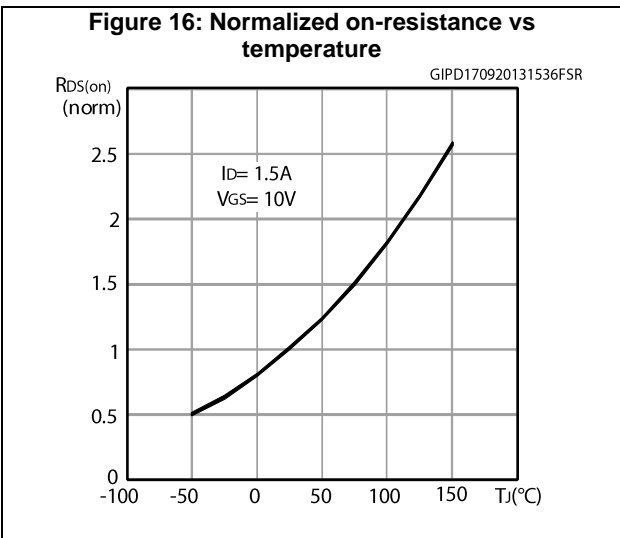
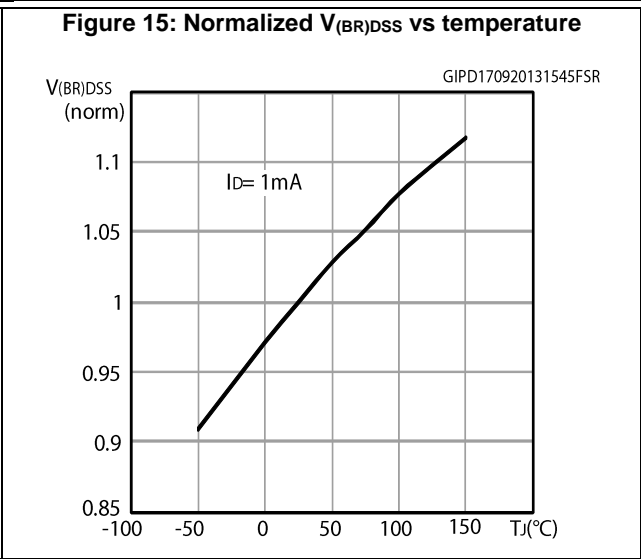
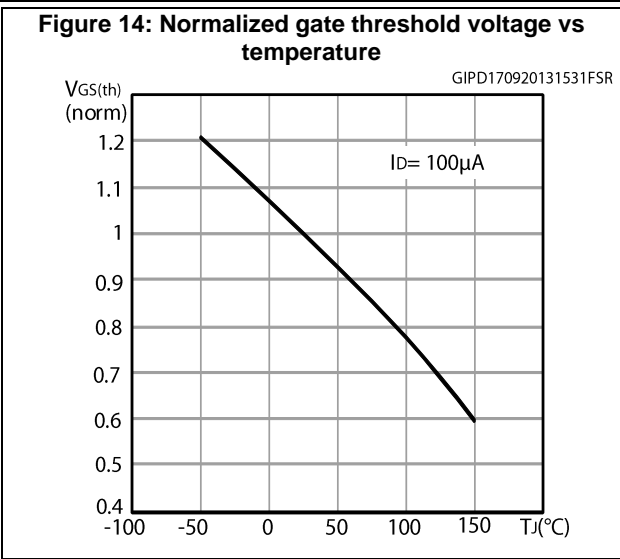
Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ , $I_D = 0\text{ A}$	30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

## 2.1 Electrical characteristics (curves)



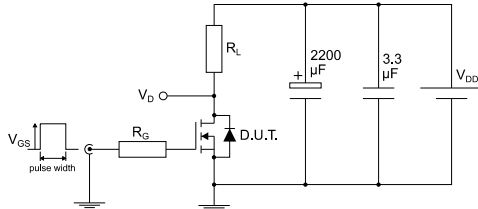






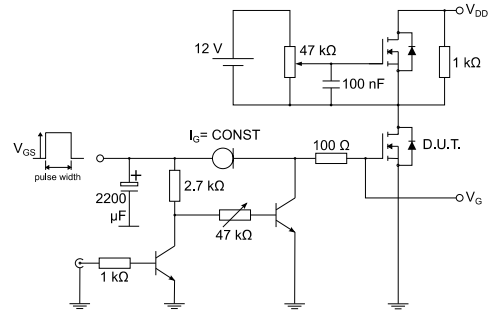
### 3 Test circuits

**Figure 18: Test circuit for resistive load switching times**



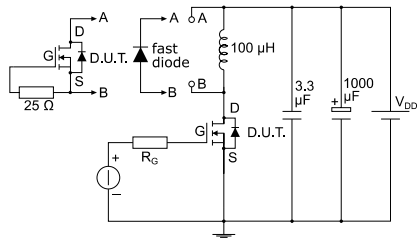
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**Figure 19: Test circuit for gate charge behavior**



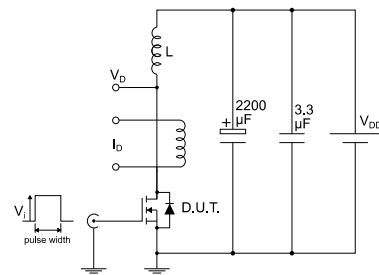
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**Figure 20: Test circuit for inductive load switching and diode recovery times**



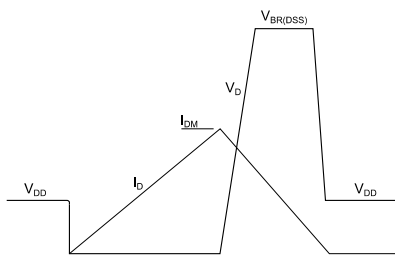
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**Figure 21: Unclamped inductive load test circuit**



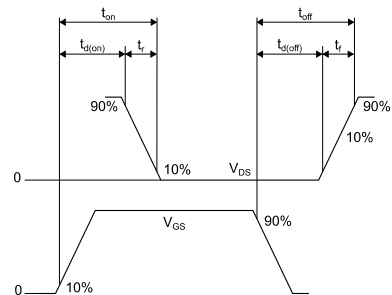
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**Figure 22: Unclamped inductive waveform**



AM01472v1

**Figure 23: Switching time waveform**



AM01473v1

## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 DPAK (TO-252) type A2 package information

Figure 24: DPAK (TO-252) type A2 package outline

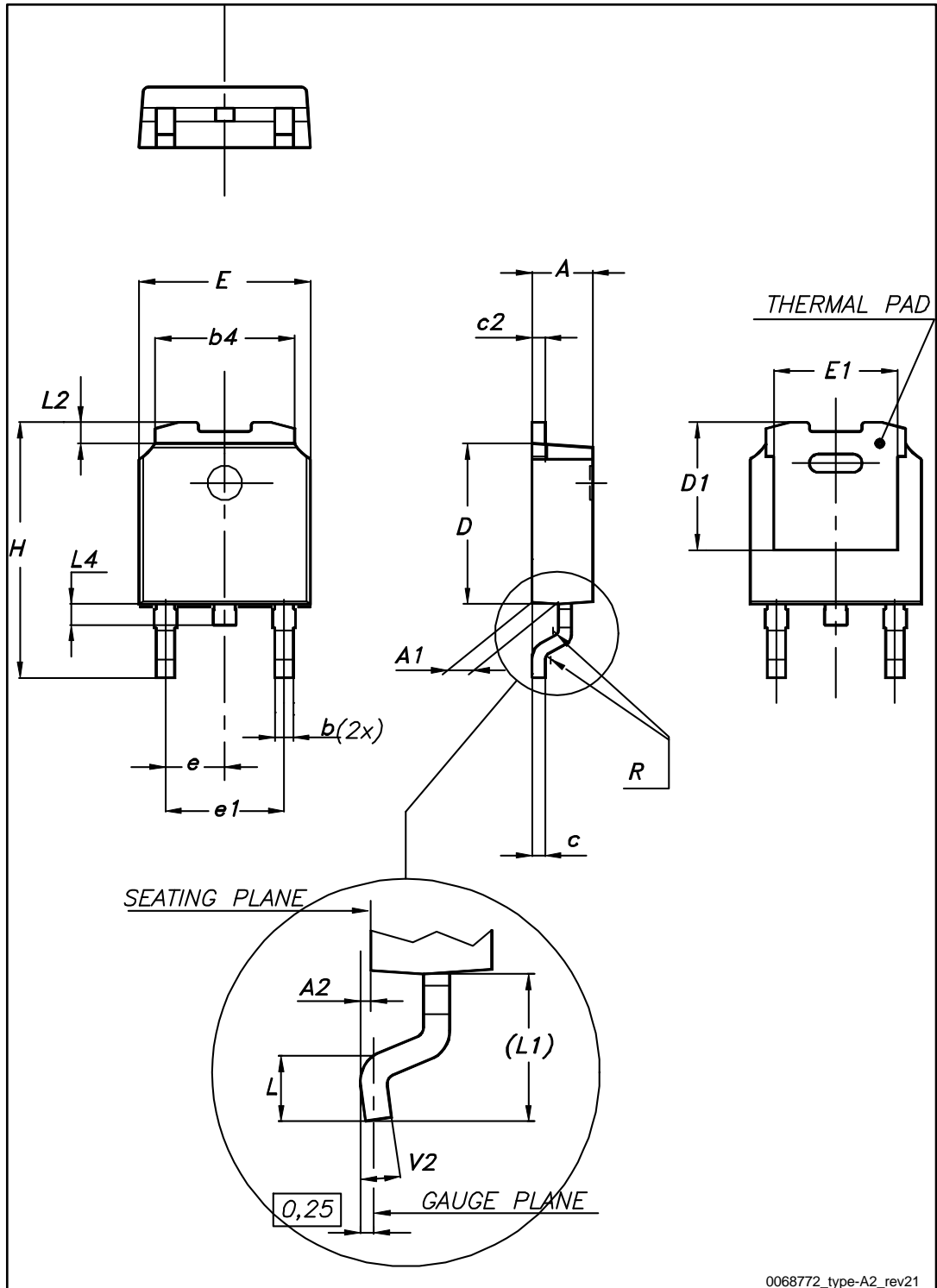
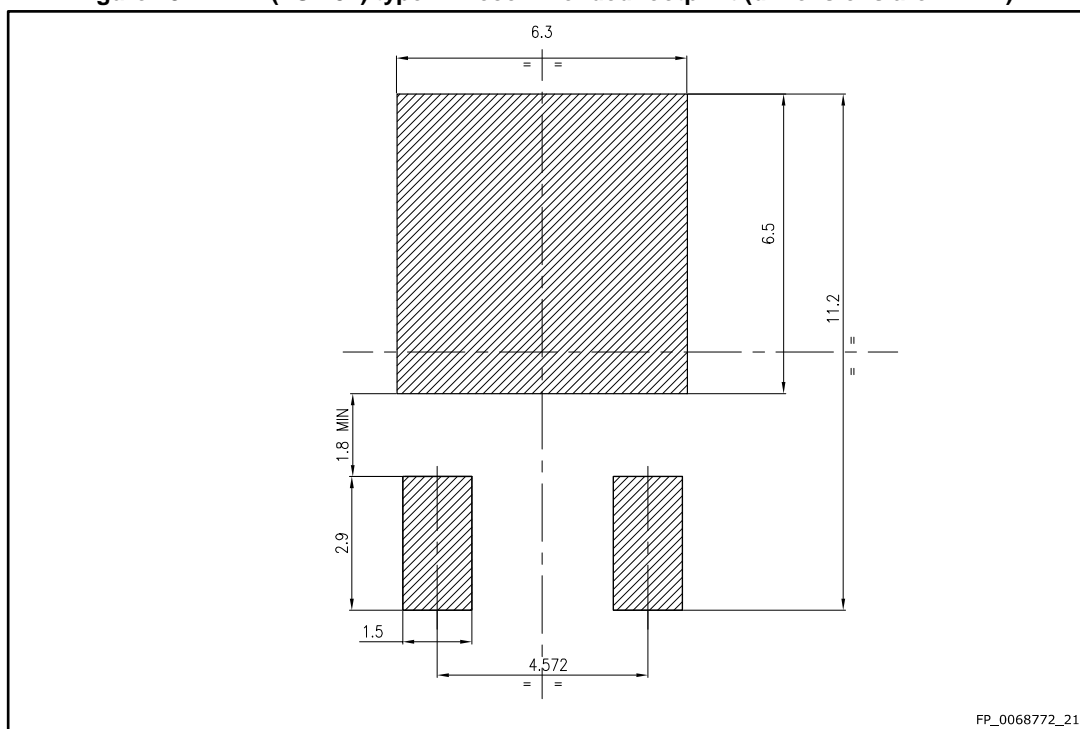


Table 10: DPAK (TO-252) type A2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 25: DPAK (TO-252) type A2 recommended footprint (dimensions are in mm)



### 4.2 DPAK (TO-252) type C2 package information

Figure 26: DPAK (TO-252) type C2 package outline

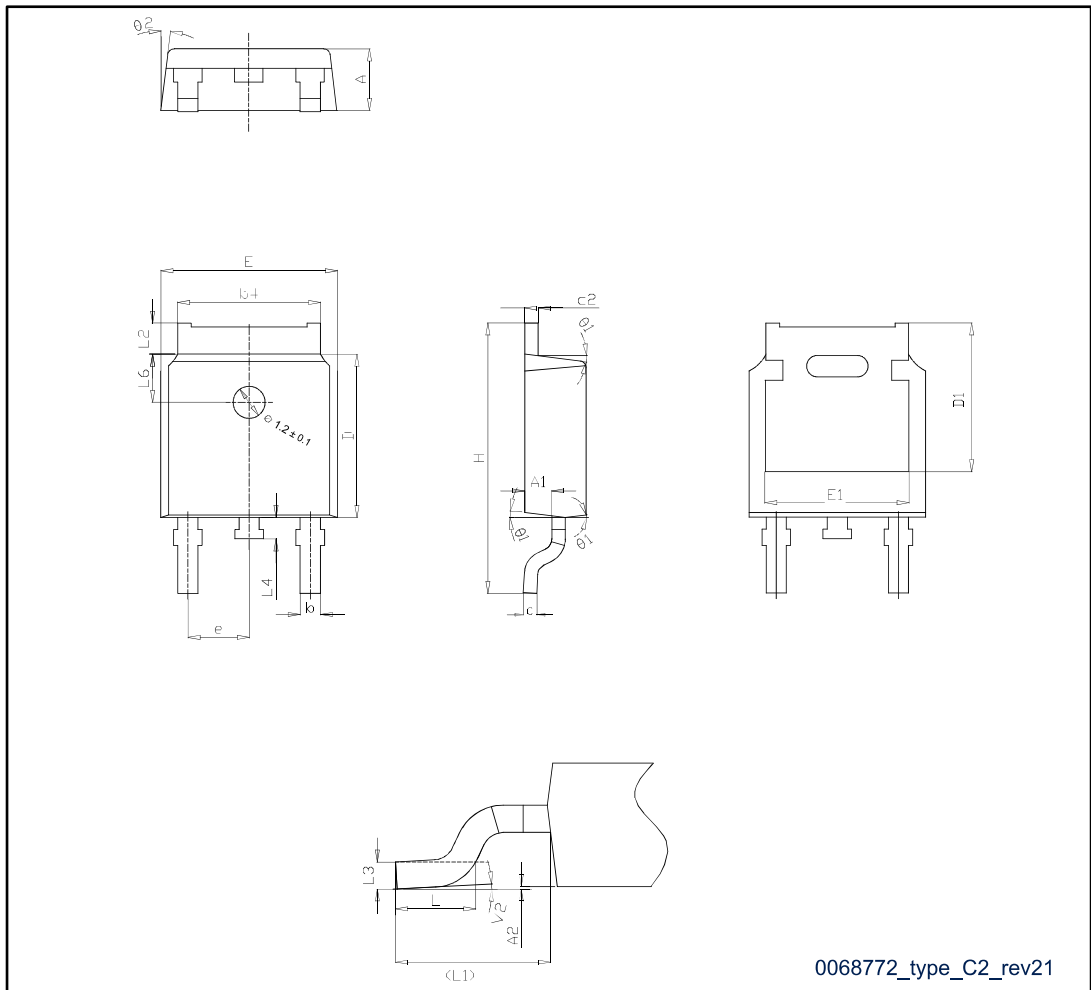
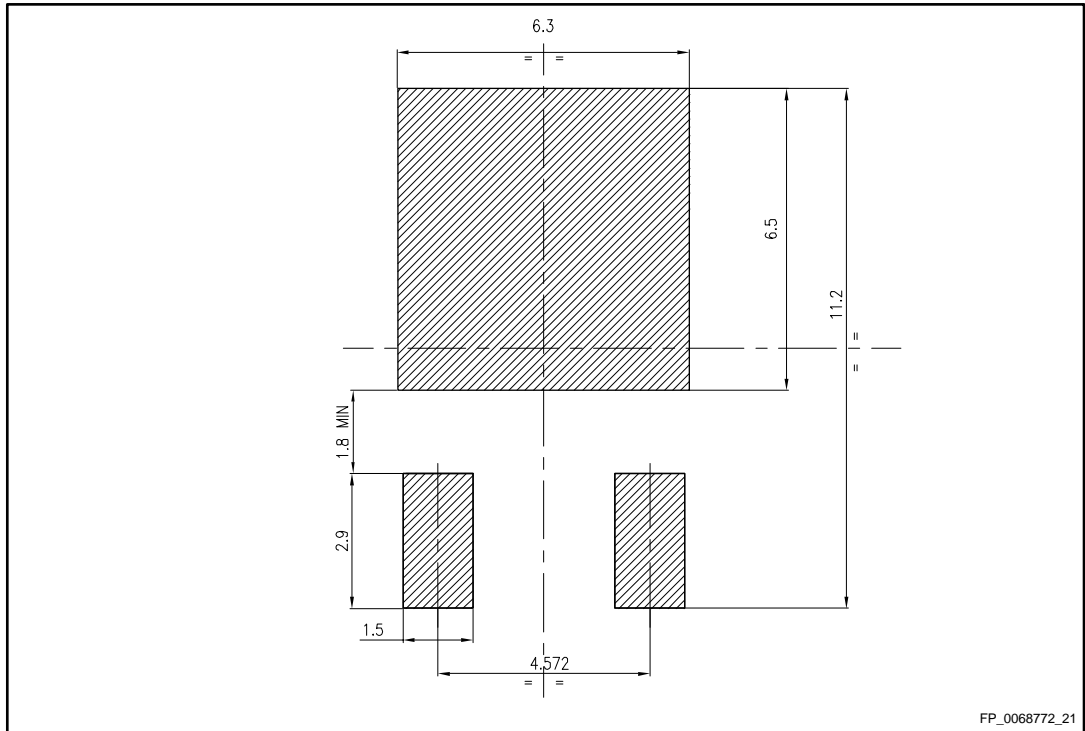


Table 11: DPAK (TO-252) type C2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.10		5.60
E	6.50	6.60	6.70
E1	5.20		5.50
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

Figure 27: DPAK (TO-252) type C2 recommended footprint (dimensions are in mm)





### 4.3 DPAK (TO-252) packing information

Figure 28: DPAK (TO-252) tape outline

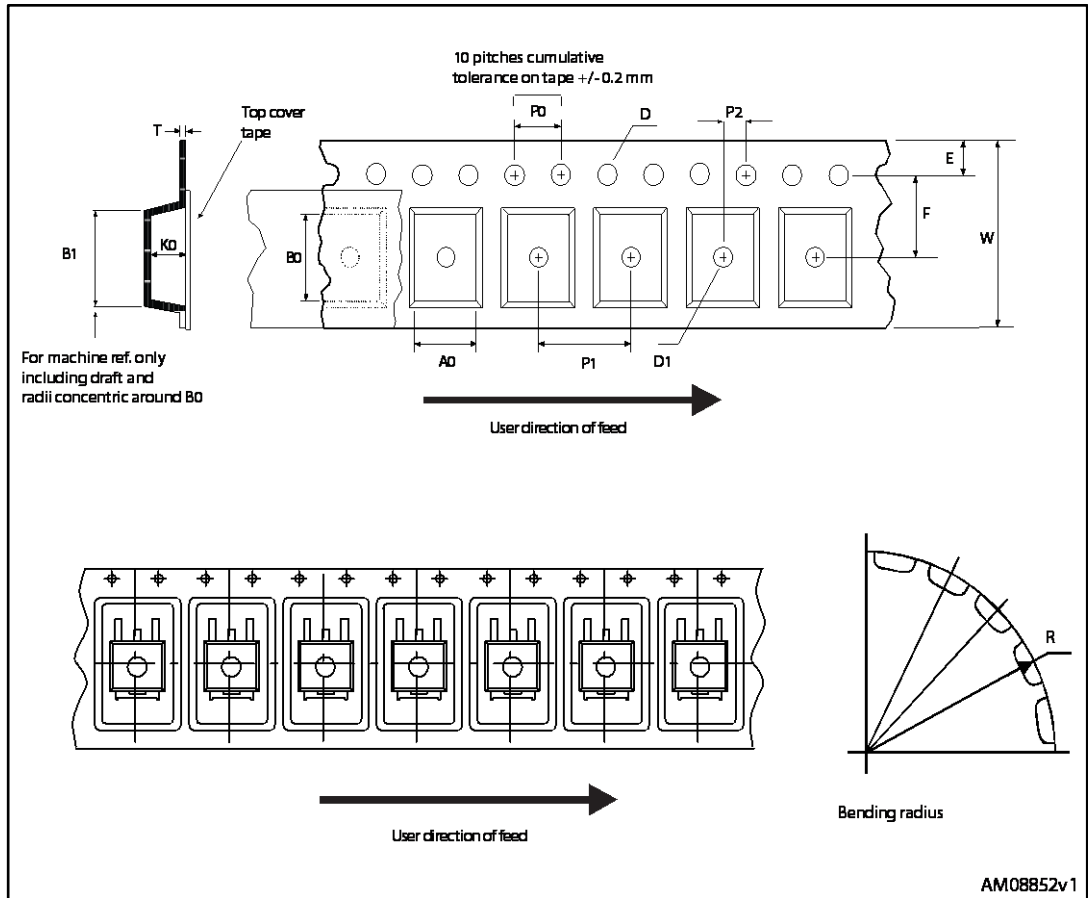


Figure 29: DPAK (TO-252) reel outline

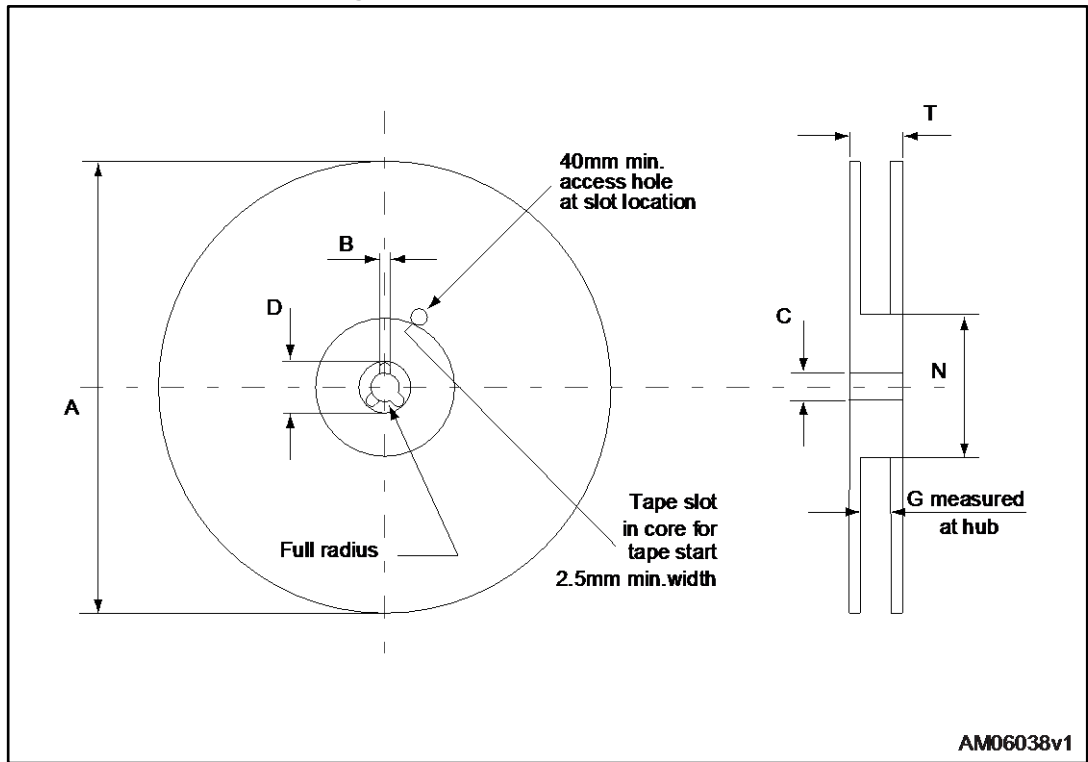
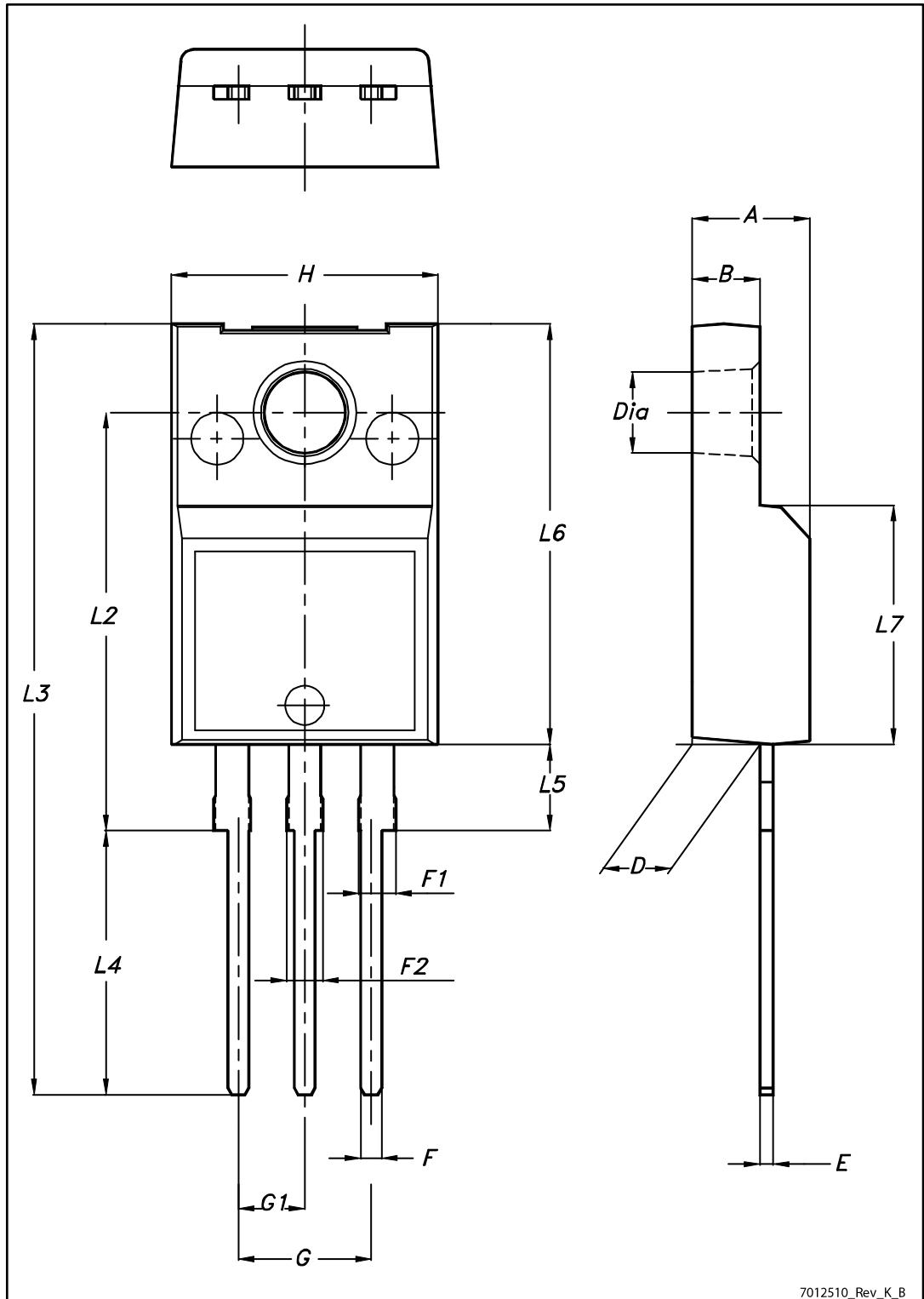


Table 12: DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

### 4.4 TO-220FP package information

Figure 30: TO-220FP package outline



7012510\_Rev\_K\_B

Table 13: TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

### 4.5 TO-220 type A package information

Figure 31: TO-220 type A package outline

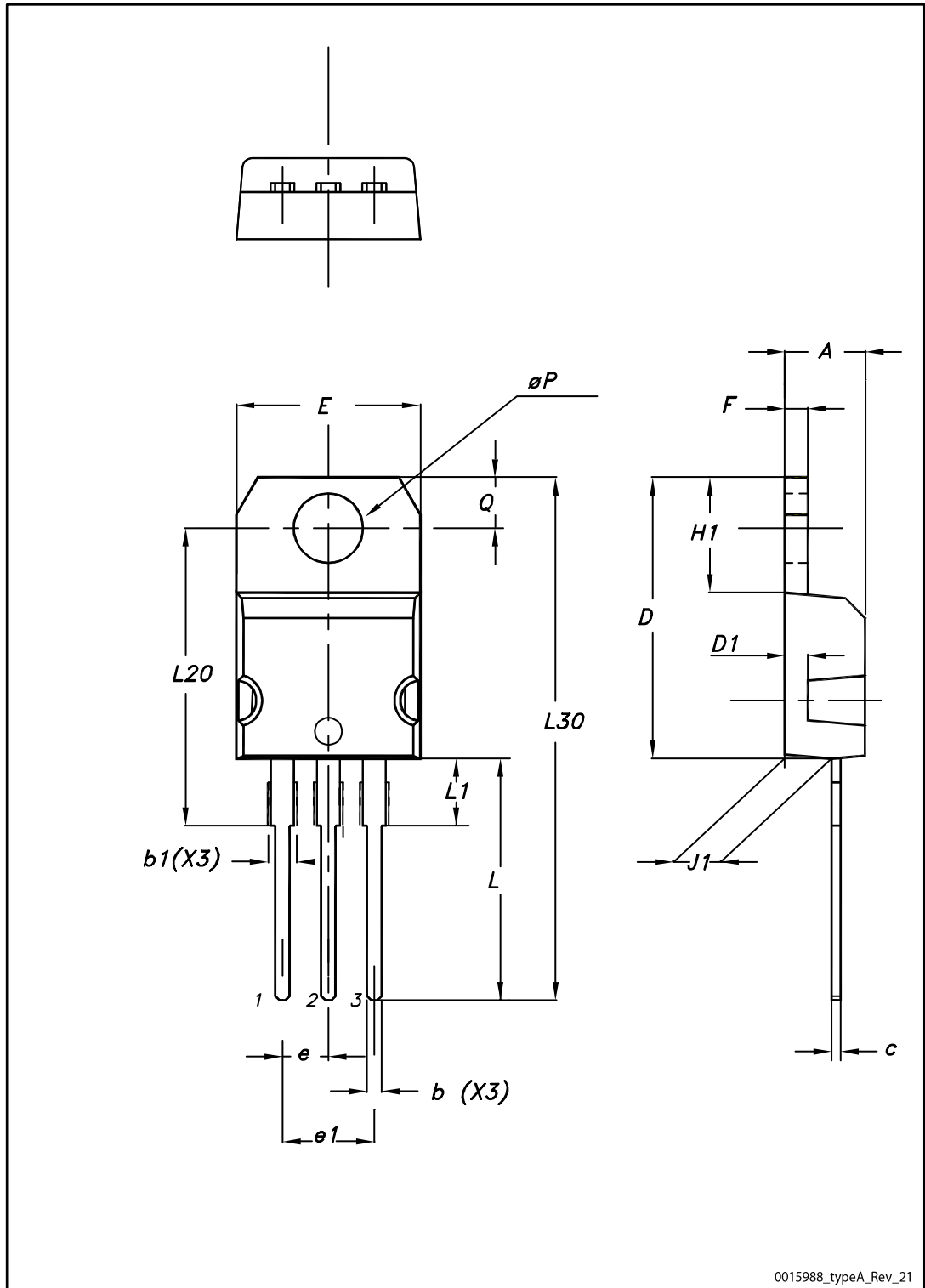


Table 14: TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

### 4.6 IPAK (TO-251) type A package information

Figure 32: IPAK (TO-251) type A package outline

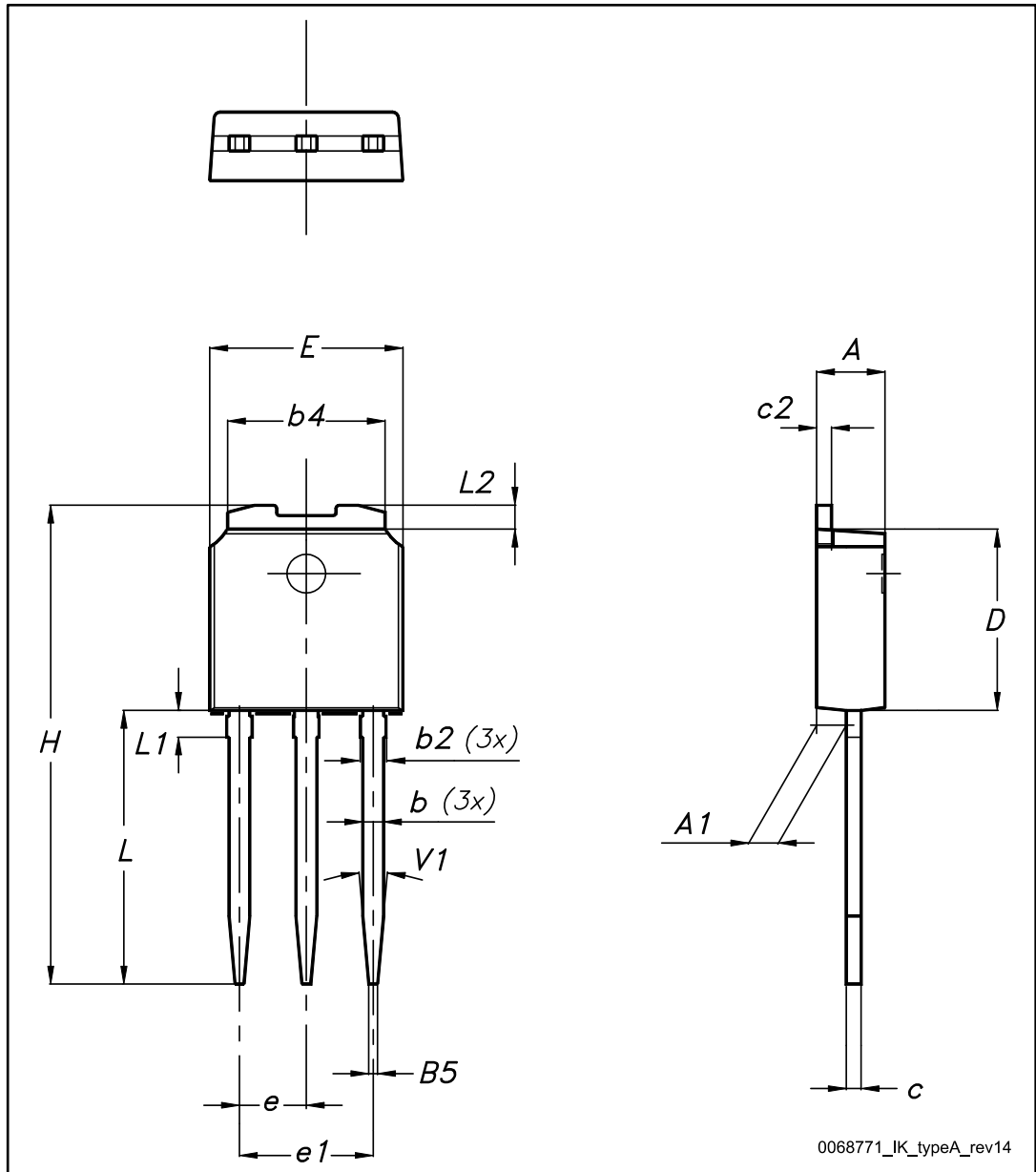


Table 15: IPAK (TO-251) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	



## 5 Revision history

Table 16: Document revision history

Date	Revision	Changes
08-May-2013	1	First release.
18-Sep-2013	2	Document status promoted from preliminary to production data. Added <i>Section 2.1: Electrical characteristics (curves)</i> . Updated DPAK mechanical data.
25-Sep-2013	3	Inserted <i>Figure 17: Source-drain diode forward characteristics</i> .
04-Jan-2017	4	Added IPAK package. Modified title, features and description on cover page. Modified <i>Table 2: "Absolute maximum ratings"</i> , <i>Table 3: "Thermal data"</i> , <i>Table 5: "On/off-state"</i> . Modified <i>Figure 11: "Static drain-source on-resistance"</i> . Updated <i>Section 4: "Package information"</i> . Minor text changes.

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